

- [0015] Figures 3a and 3b illustrate a plan view and a cross section, respectively, in the longitudinal direction through a fin field-effect transistor in a first phase of formation, in accordance with an exemplary embodiment of the present invention.
- [0016] Figures 4a and 4b illustrate a plan view and a cross section, respectively, in the longitudinal direction through a fin field-effect transistor according to the invention in a second phase of formation, in accordance with an exemplary embodiment of the present invention,
- [0017] Figures 5^a and 5b illustrate a plan view and a cross section, respectively, in the longitudinal direction through a fin field-effect transistor in a third phase of formation, in accordance with an exemplary embodiment of the present invention,
- [0018] Figures 6a and 6b illustrate a plan view and a cross section, respectively, in the longitudinal direction through a fin field-effect transistor in a fourth phase of formation, in accordance with an exemplary embodiment of the present invention.
- [0019] Figures 7a and 7b illustrate a plan view and a cross section, respectively, in the longitudinal direction through a fin field-effect transistor in a fifth phase of formation, in accordance with an exemplary embodiment of the present invention.
- [0020] Figure 8 illustrates diagrammatically a fin field-effect transistor according to a preferred embodiment of the present invention.
- [0021] Figure 9 illustrates diagrammatically a conventional fin field-effect transistor.
- [0022] Figure 10 illustrates a diagrammatic comparison between an arrangement of fin field-effect transistors according to an embodiment of the present invention and an arrangement of fin field-effect transistors of a known type.